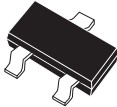


## CMPT4033

### PNP SILICON TRANSISTOR



**SOT-23 CASE**

### DESCRIPTION

The CENTRAL SEMICONDUCTOR CMPT4033 type is an PNP silicon transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for very high current, general purpose amplifier applications.

**Marking Code is C4A.**

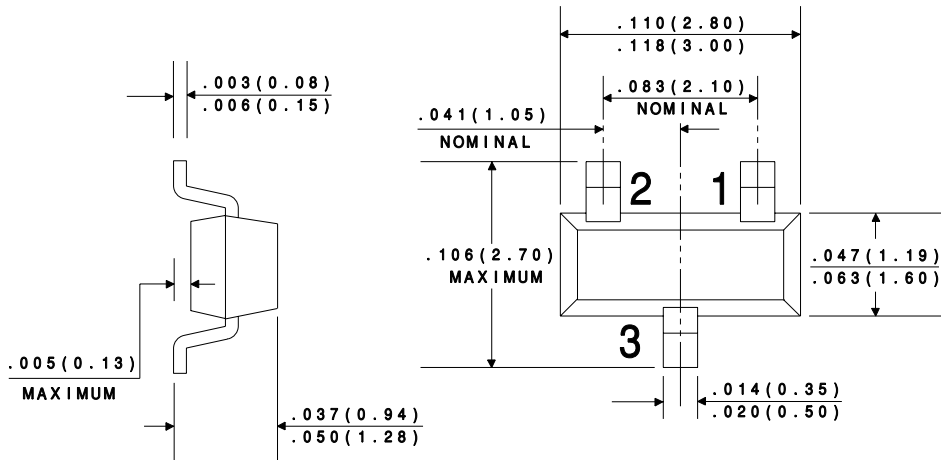
### MAXIMUM RATINGS (T<sub>A</sub>=25°C)

	SYMBOL		UNITS
Collector-Base Voltage	V <sub>CBO</sub>	80	V
Collector-Emitter Voltage	V <sub>CEO</sub>	80	V
Emitter-Base Voltage	V <sub>EBO</sub>	5.0	V
Collector Current	I <sub>C</sub>	500	mA
Collector Current (Peak)	I <sub>CM</sub>	1.0	A
Power Dissipation	P <sub>D</sub>	350	mW
Operating and Storage			
Junction Temperature	T <sub>J</sub> , T <sub>stg</sub>	-65 to +150	°C
Thermal Resistance	θ <sub>JA</sub>	357	°C/W

### ELECTRICAL CHARACTERISTICS (T<sub>A</sub>=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I <sub>CBO</sub>	V <sub>CB</sub> =60V		50	nA
I <sub>EBO</sub>	V <sub>EB</sub> =5.0V		10	nA
BV <sub>CBO</sub>	I <sub>C</sub> =10μA	80		V
BV <sub>CEO</sub>	I <sub>C</sub> =10mA	80		V
BV <sub>EBO</sub>	I <sub>E</sub> =10μA	5.0		V
V <sub>CE(SAT)</sub>	I <sub>C</sub> =150mA, I <sub>B</sub> =15mA		0.15	V
V <sub>CE(SAT)</sub>	I <sub>C</sub> =500mA, I <sub>B</sub> =50mA		0.50	V
V <sub>BE(SAT)</sub>	I <sub>C</sub> =150mA, I <sub>B</sub> =15mA		0.90	V
V <sub>BE(SAT)</sub>	I <sub>C</sub> =500mA, I <sub>B</sub> =50mA		1.10	V
h <sub>FE</sub>	V <sub>CE</sub> =5.0V, I <sub>C</sub> =0.1mA	75		
h <sub>FE</sub>	V <sub>CE</sub> =5.0V, I <sub>C</sub> =100mA	100	300	
h <sub>FE</sub>	V <sub>CE</sub> =5.0V, I <sub>C</sub> =500mA	70		
f <sub>T</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =50mA, f=1.0MHz	100		MHz
C <sub>ob</sub>	V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=1.0MHz		20	pF
C <sub>ib</sub>	V <sub>EB</sub> =0.5V, I <sub>C</sub> =0, f=1.0MHz		110	pF

All dimensions in inches (mm).



LEAD CODE:

- 1) BASE
- 2) EMITTER
- 3) COLLECTOR